

Title (en)

CRUCIBLE FOR CRYSTALLIZATION OF MOLTEN SILICON, PROCESS FOR ITS MANUFACTURE AND USE THEREOF

Title (de)

TIEGEL ZUR KRISTALLISIERUNG VON GESCHMOLZENEM SILICIUM, VERFAHREN ZU DESSEN HERSTELLUNG UND VERWENDUNG DAVON

Title (fr)

CREUSET POUR LA CRISTALLISATION DE SILICIUM FONDU, PROCÉDÉ DE FABRICATION ET SON UTILISATION

Publication

EP 3494247 A1 20190612 (EN)

Application

EP 17746135 A 20170803

Priority

- EP 16182660 A 20160803
- EP 2017069661 W 20170803

Abstract (en)

[origin: WO2018024830A1] Crucible for the crystallization of molten silicon coated with silicon nitride where embedded SiO₂ particles having a particle size up to 500 µm and a surface density ≥ 100 cm⁻², emerge in the inner volume of the crucible enabling the production of silicon ingot with improved electrical properties.

IPC 8 full level

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CPC (source: EP)

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Citation (search report)

See references of WO 2018024830A1

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